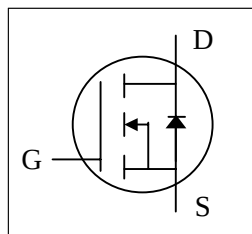


- ▼ 100% R_g & UIS Test
- ▼ Simple Drive Requirement
- ▼ Ultra Low On-resistance
- ▼ RoHS Compliant & Halogen-Free

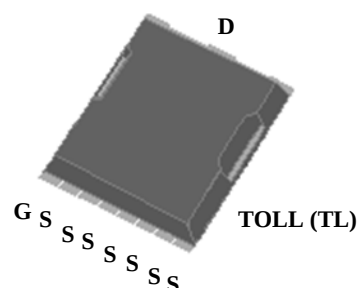


BV_{DSS}	100V
$R_{DS(ON)}$	2m Ω

Description

XP10NB2R0 series are innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TOLL package is a perfect solution for high power density and high power efficiency application.



Absolute Maximum Ratings@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Drain Current, V_{GS} @ 10V	247	A
$I_D@T_C=100^\circ\text{C}$	Drain Current, V_{GS} @ 10V	175	A
I_{DM}	Pulsed Drain Current ¹	1000	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	250	W
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	3.75	W
E_{AS}	Single Pulse Avalanche Energy ⁵	500	mJ
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Units
R_{thj-c}	Maximum Thermal Resistance, Junction-case	0.6	$^\circ\text{C}/\text{W}$
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient (PCB mount) ³	40	$^\circ\text{C}/\text{W}$

Electrical Characteristics@T_J=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =100A	-	-	2	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2	-	4	V
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =100A	-	210	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V	-	-	25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} = ±20V, V _{DS} =0V	-	-	±0.1	uA
Q _g	Total Gate Charge ⁴	I _D =100A	-	136	217.6	nC
Q _{gs}	Gate-Source Charge ⁴	V _{DS} =50V	-	36	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge ⁴	V _{GS} =10V	-	42	-	nC
t _{d(on)}	Turn-on Delay Time ⁴	V _{DS} =50V	-	28	-	ns
t _r	Rise Time ⁴	I _D =100A	-	115	-	ns
t _{d(off)}	Turn-off Delay Time ⁴	R _G =6Ω	-	91	-	ns
t _f	Fall Time ⁴	V _{GS} =10V	-	218	-	ns
C _{iss}	Input Capacitance ⁴	V _{GS} =0V	-	7600	12160	pF
C _{oss}	Output Capacitance ⁴	V _{DS} =80V	-	1085	-	pF
C _{rss}	Reverse Transfer Capacitance ⁴	f=1.0MHz	-	30	-	pF
R _g	Gate Resistance	f=1.0MHz	-	0.6	1.2	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =100A, V _{GS} =0V	-	-	1.3	V
t _{rr}	Reverse Recovery Time ⁴	I _S =100A, V _{GS} =0V	-	118	-	ns
Q _{rr}	Reverse Recovery Charge ⁴	dI/dt=100A/μs	-	225	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board
- 4.Guaranteed by design.
- 5.Starting T_J=25°C , V_{DD}=50V , L=0.1mH , R_G=25Ω , V_{GS}=10V
- 6.These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT, AUTOMOTIVE OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

XSEMI DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

XSEMI RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.

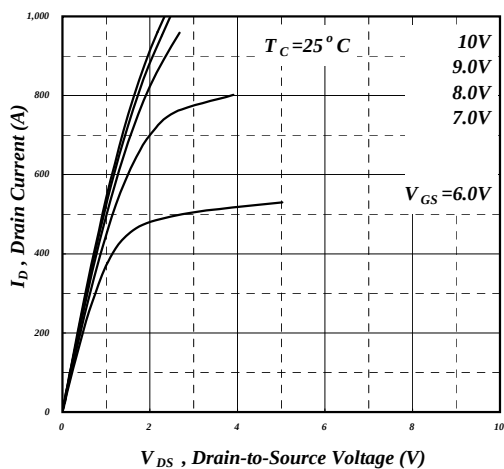


Fig 1. Typical Output Characteristics

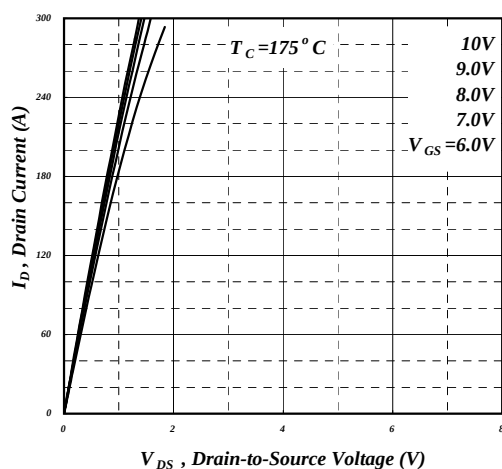


Fig 2. Typical Output Characteristics

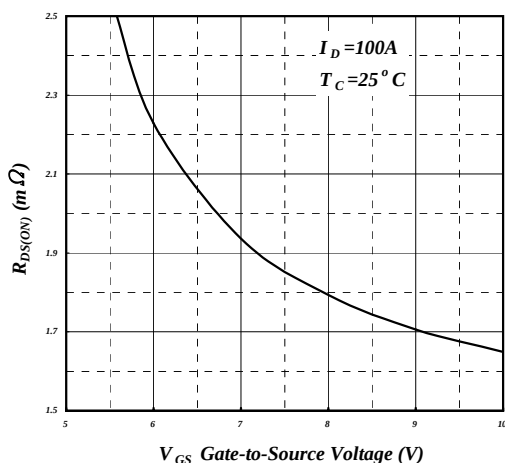
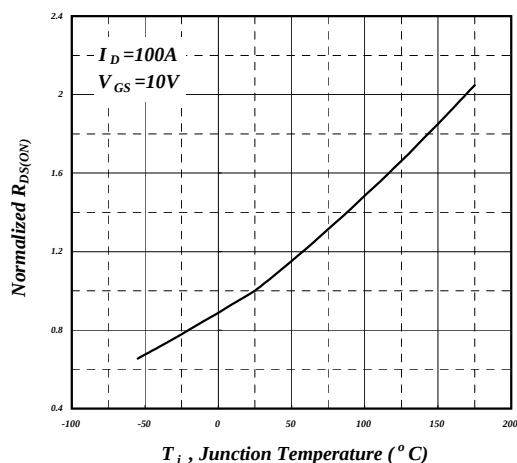
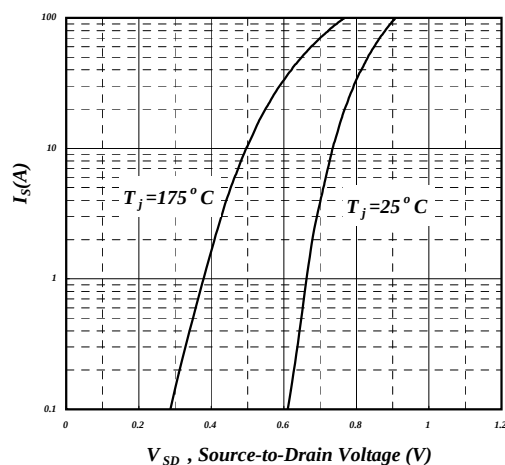


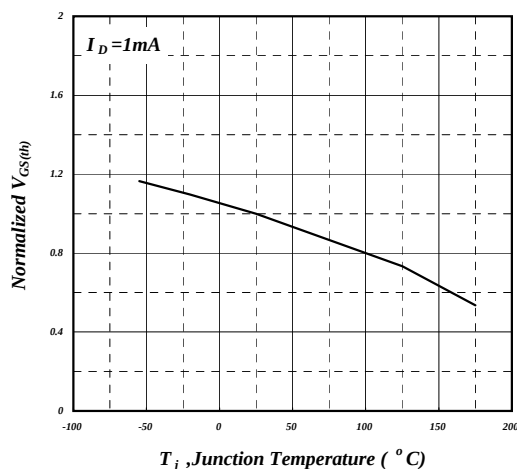
Fig 3. On-Resistance v.s. Gate Voltage



**Fig 4. Normalized On-Resistance
v.s. Junction Temperature**



**Fig 5. Forward Characteristic of
Reverse Diode**



**Fig 6. Gate Threshold Voltage v.s.
Junction Temperature**

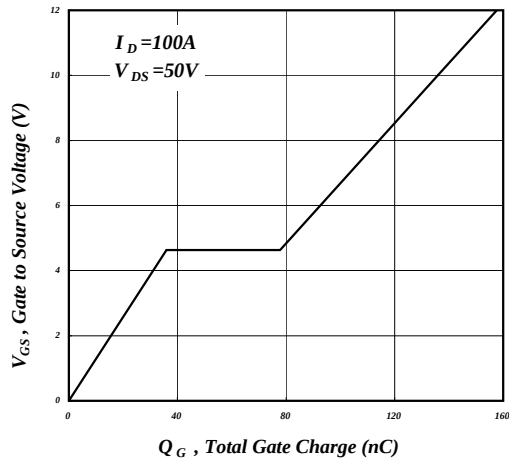


Fig 7. Gate Charge Characteristics

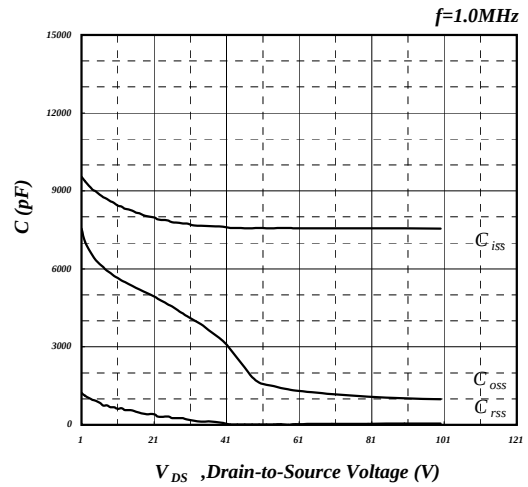


Fig 8. Typical Capacitance Characteristics

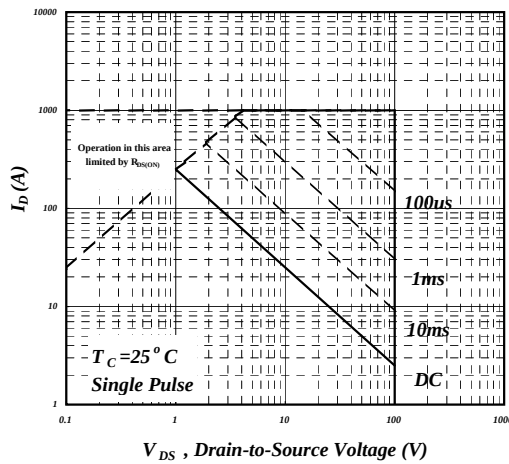


Fig 9. Maximum Safe Operating Area⁶

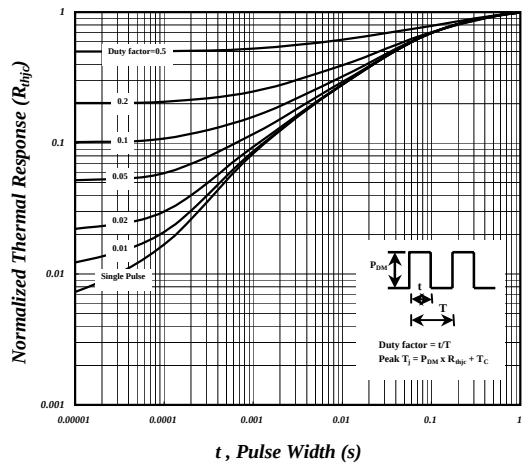


Fig 10. Effective Transient Thermal Impedance

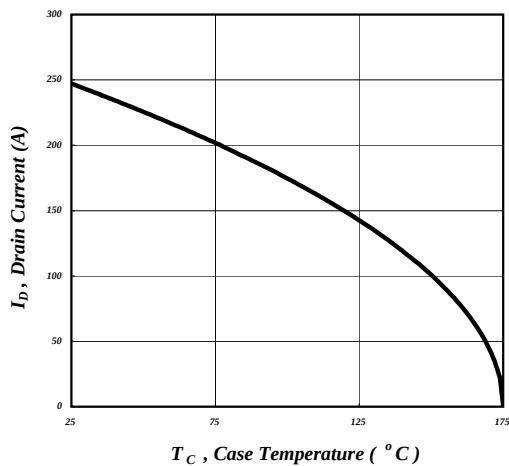


Fig 11. Drain Current v.s. Case Temperature

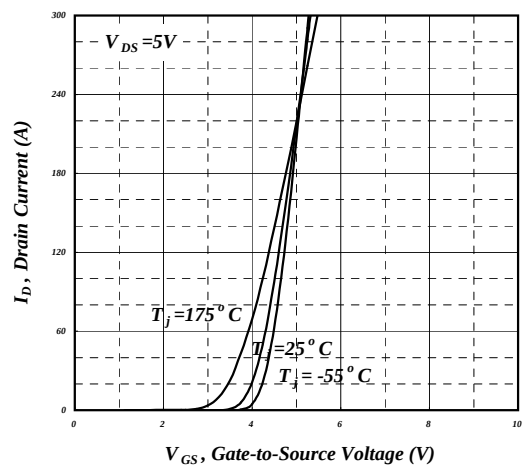


Fig 12. Transfer Characteristics

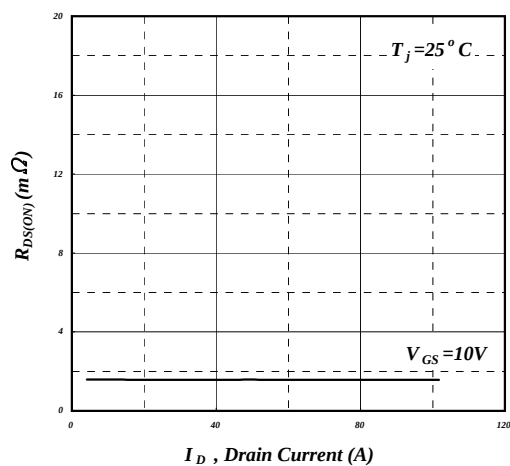


Fig 13. Typ. Drain-Source on State Resistance

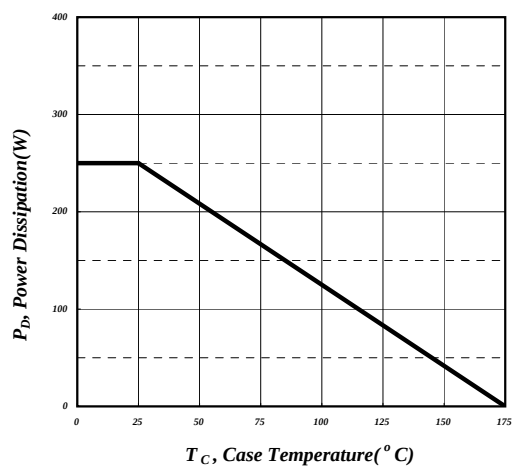
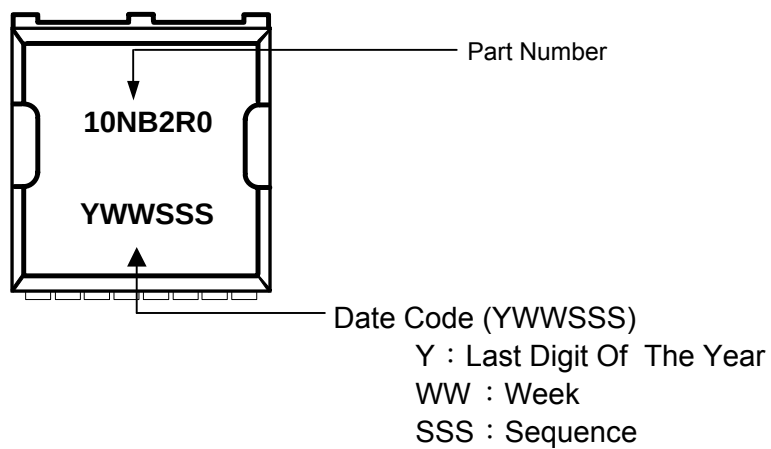
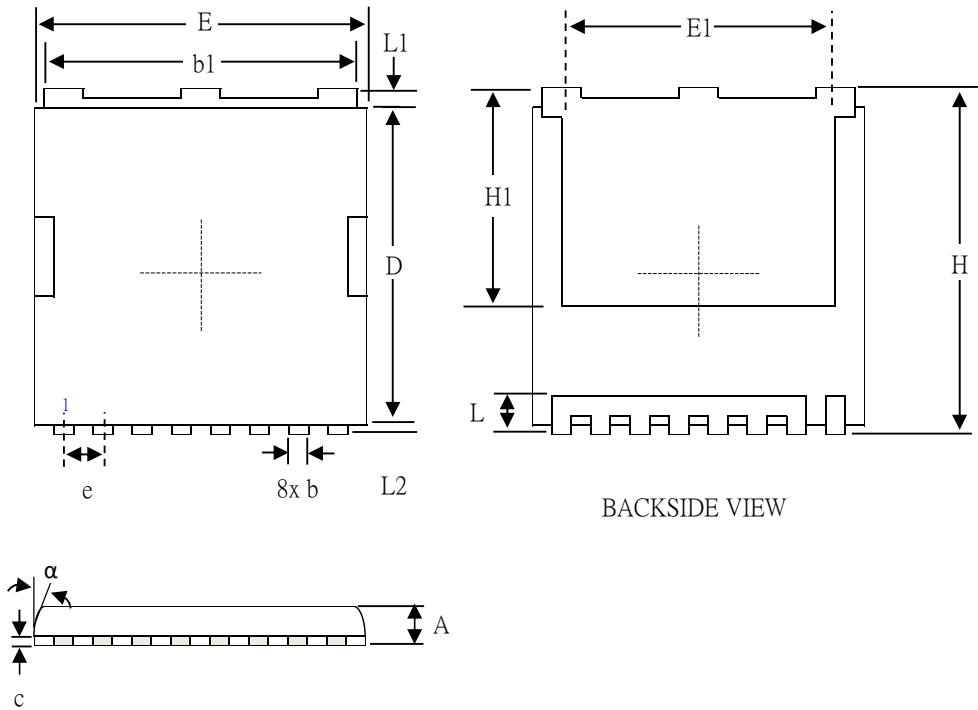


Fig 14. Total Power Dissipation

MARKING INFORMATION

Package Outline : TOLL



SYMBOLS	MIN	NOM	MAX
A	2.20	2.30	2.40
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
c	0.40	0.50	0.60
D	10.28	10.38	10.58
E	9.70	9.90	10.10
E1	7.90	8.70	9.50
e	1.20BCS		
H	11.48	11.68	11.88
H1	6.75	-	7.43
L	1.40	1.90	2.10
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
α	10° REF.		

- 1.All dimension are in millimeters.
- 2.Dimension does not include burrs and mold flash/protrusions.
- 3.The outline schematic is not to scale and slightly different from the actual product appearance.

TOLL FOOTPRINT :

